

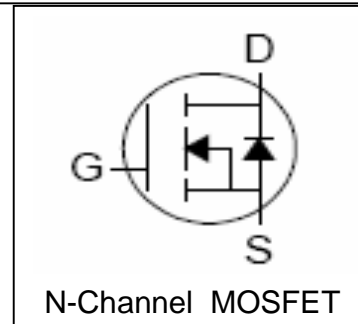
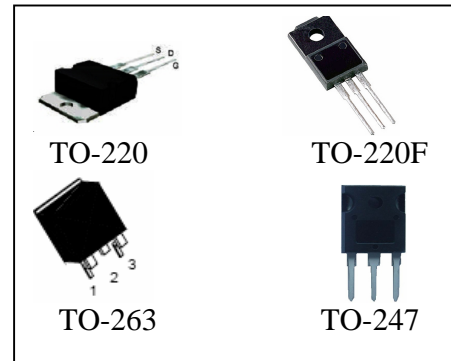
Features

- 150V/120A
 $R_{DS(ON)}=15m\Omega(Typ.) @ V_{GS}=10V$
- Avalanche Rated
- Reliable and Rugged
- Lead Free and Green Devices Available

Applications

- Automotive applications and a wide variety of other applications
- High Efficiency Synchronous in SMPS
- High Speed Power Switching

Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_A=25^\circ C$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	150	V
V_{GSS}	Gate-Source Voltage	± 25	
T_J	Maximum Junction Temperature	175	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
I_S	Diode Continuous Forward Current	$T_C=25^\circ C$ 120	A
Mounted on Large Heat Sink			
I_{DP}	300 μs Pulsed Drain Current Tested	$T_C=25^\circ C$ 400 ^①	A
I_D	Continue Drain Current	$T_C=25^\circ C$ 120 ^②	
		$T_C=100^\circ C$ 100	
P_D	Maximum Power Dissipation	$T_C=25^\circ C$ 400	W
		$T_C=100^\circ C$ 220	
$R_{\theta JC}$	Thermal Resistance -Junction to Case	0.45	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62.5	
Drain-Source Avalanche Ratings			
E_{AS}	Avalanche Energy ,Single Pulsed	2000	mJ

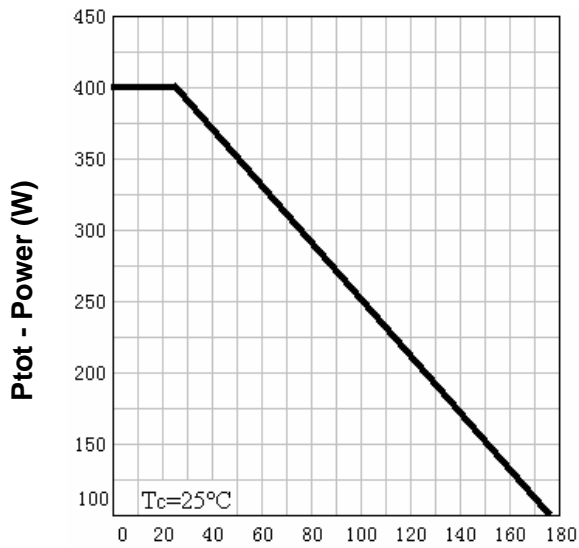
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU120N15			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	150			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=150V, V_{GS}=0V$ $T_J=85^{\circ}\text{C}$			1	μA
					30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2	3	4	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(3)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=60A$		15	17	$m\Omega$
Diode Characteristics						
$V_{SD}^{(3)}$	Diode Forward Voltage	$I_{SD}=60A, V_{GS}=0V$		0.8	1.3	V
t_{rr}	Reverse Recovery Time	$I_{SD}=60A, dI_{SD}/dt=100A/\mu s$		68		ns
q_{rr}	Reverse Recovery Charge			130		nC
Dynamic Characteristics ⁽⁴⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		1.0		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=30V,$ Frequency=1.0MHz		6600		pF
C_{oss}	Output Capacitance			900		
C_{rss}	Reverse Transfer Capacitance			480		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=35V, R_L=35\Omega,$ $I_{DS}=1A, V_{GEN}=10V,$ $R_G=6\Omega$		21	40	ns
t_r	Turn-on Rise Time			40	70	
$t_{d(OFF)}$	Turn-off Delay Time			110	210	
t_f	Turn-off Fall Time			69	140	
Gate Charge Characteristics ⁽⁴⁾						
Q_g	Total Gate Charge	$V_{DS}=30V, V_{GS}=10V,$ $I_{DS}=60A$		155	220	nC
Q_{gs}	Gate-Source Charge			45		
Q_{gd}	Gate-Drain Charge			48		

- Notes: ① Pulse width limited by safe operating area.
 ② Current limited by package(Limitation Current is 75A)
 ③ Pulse test ; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 ④ Guaranteed by design, not subject to production testing.

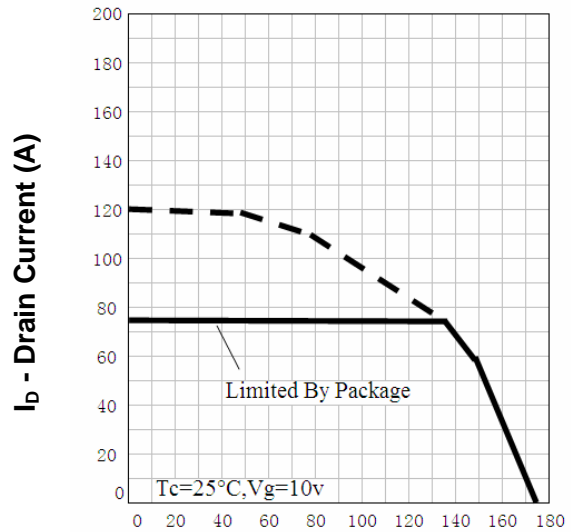
Typical Characteristics

Power Dissipation



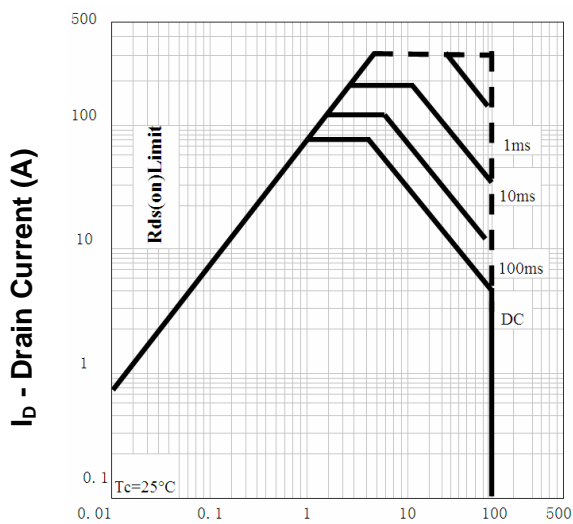
Tj - Junction Temperature (°C)

Drain Current



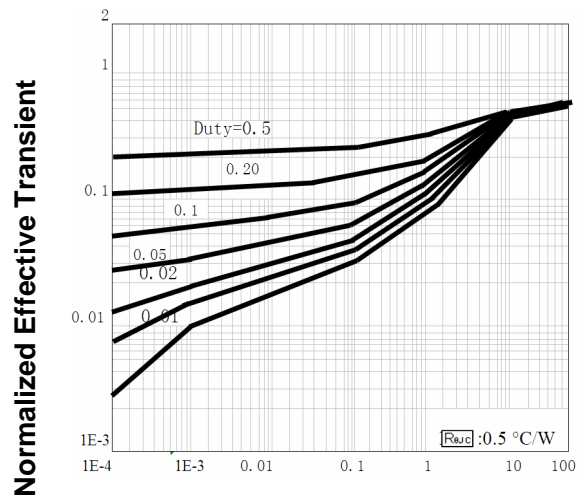
Tj - Junction Temperature (°C)

Safe Operation Area



VDS - Drain-Source Voltage (V)

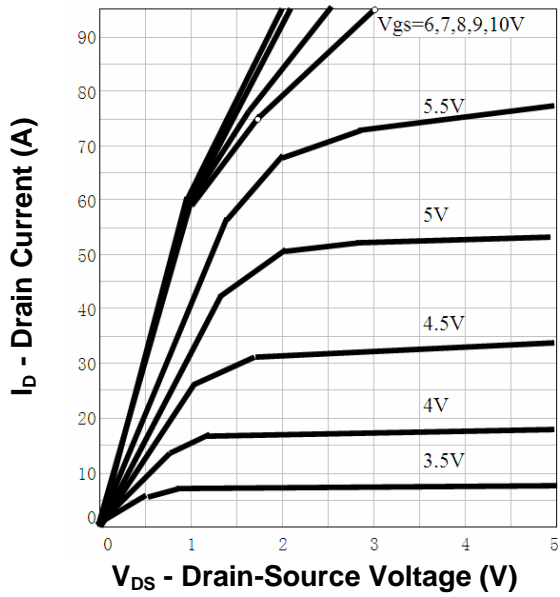
Thermal Transient Impedance



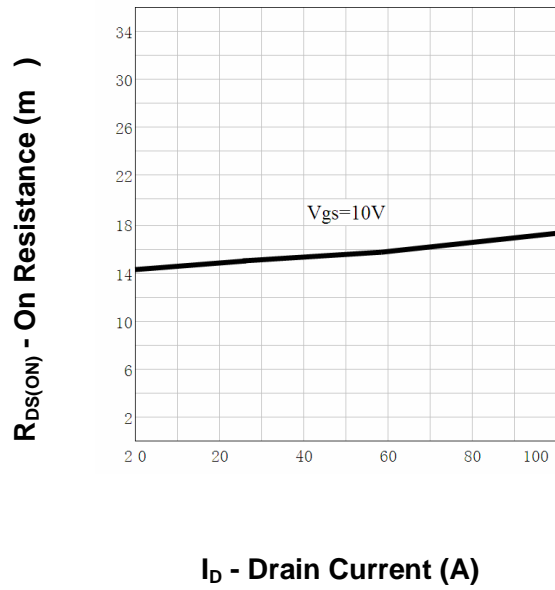
Square Wave Pulse Duration (sec)

Typical Characteristics

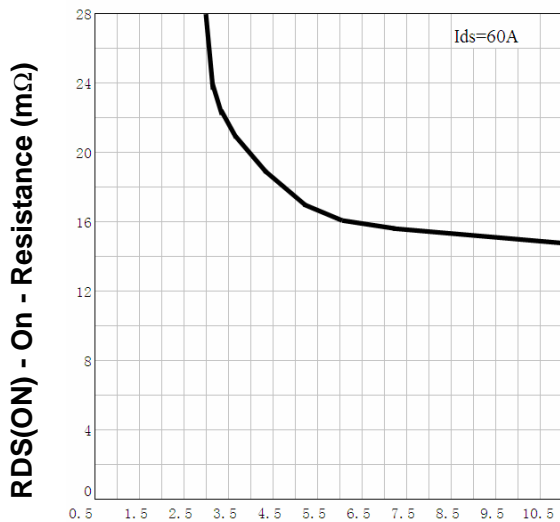
Output Characteristics
Output Characteristics



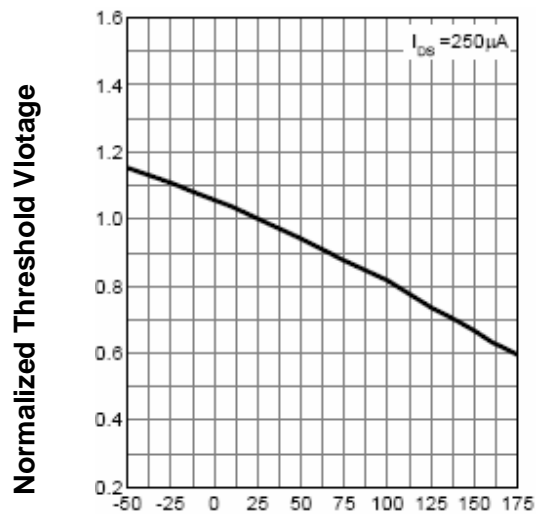
Drain-Source On Resistance



Drain-Source On Resistance



Gate Threshold Voltage

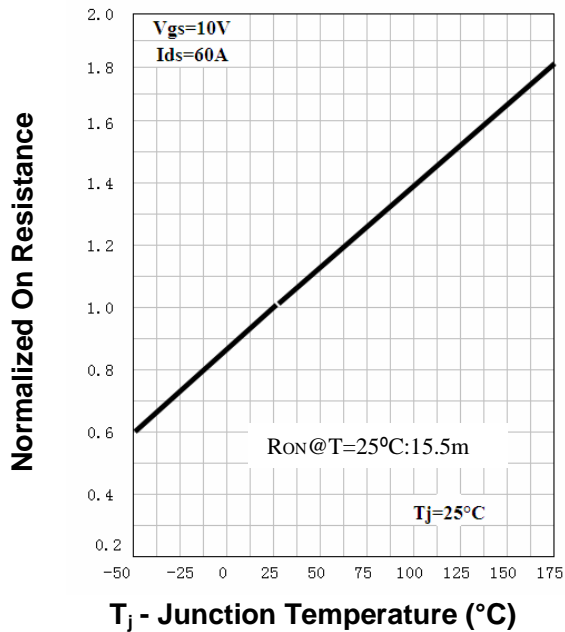


VGS - Gate - Source Voltage (V)

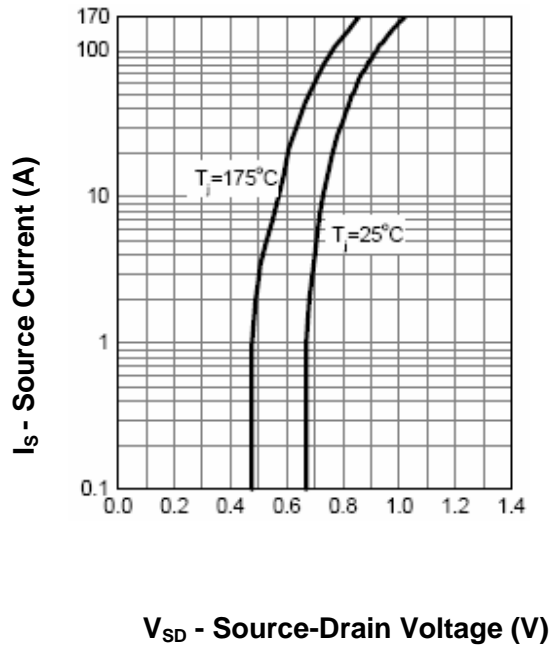
Tj - Junction Temperature ($^{\circ}C$)

Typical Characteristics

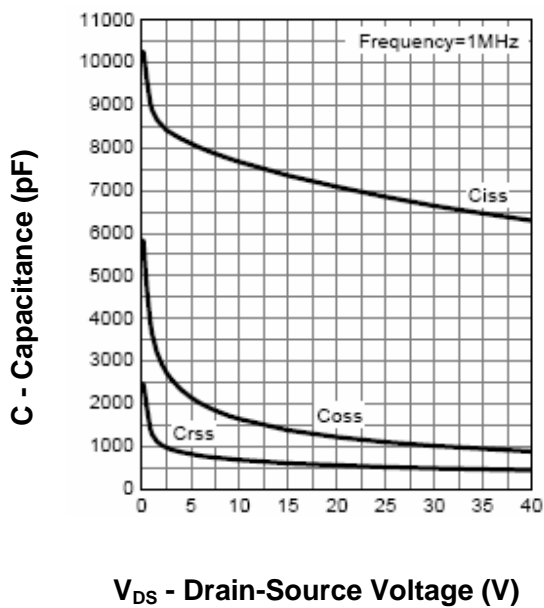
Drain-Source On Resistance



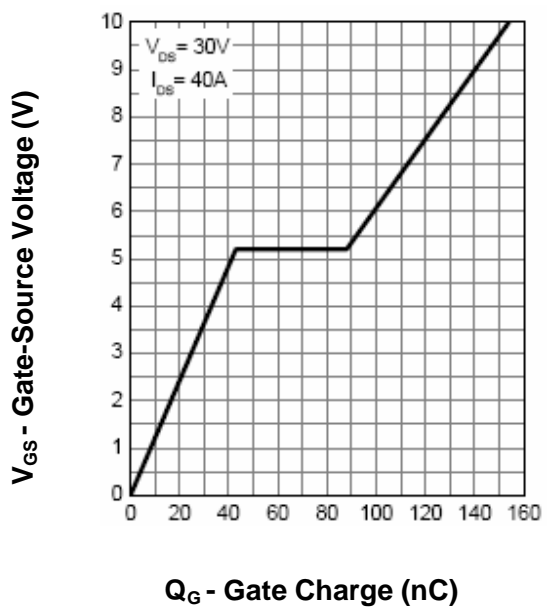
Source-Drain Diode Forward



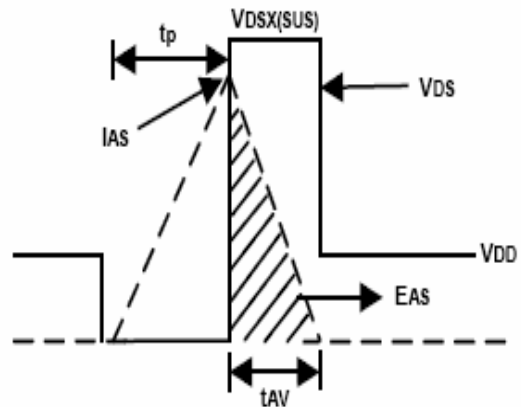
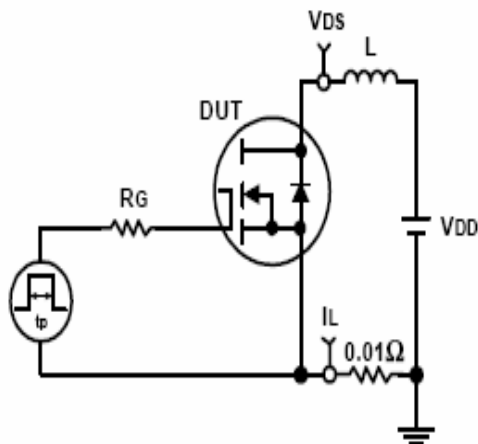
Capacitance



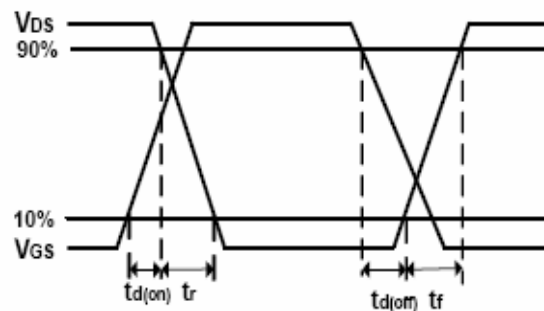
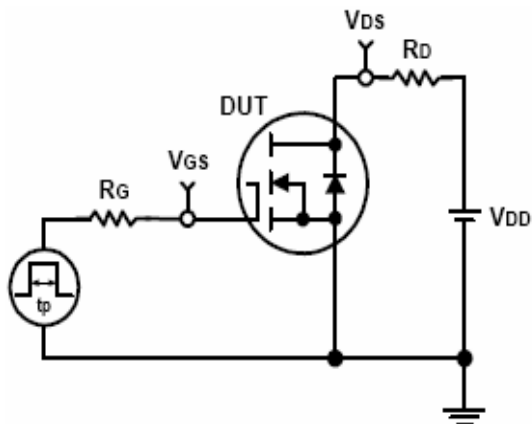
Gate Charge



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



Ordering and Marking Information**RU120N15****Package (Available)**

Q:TO-247 ; R: TO-220 ; S: TO-263

Operating Temperature Range

C : -55 to 175 °C

Assembly Material

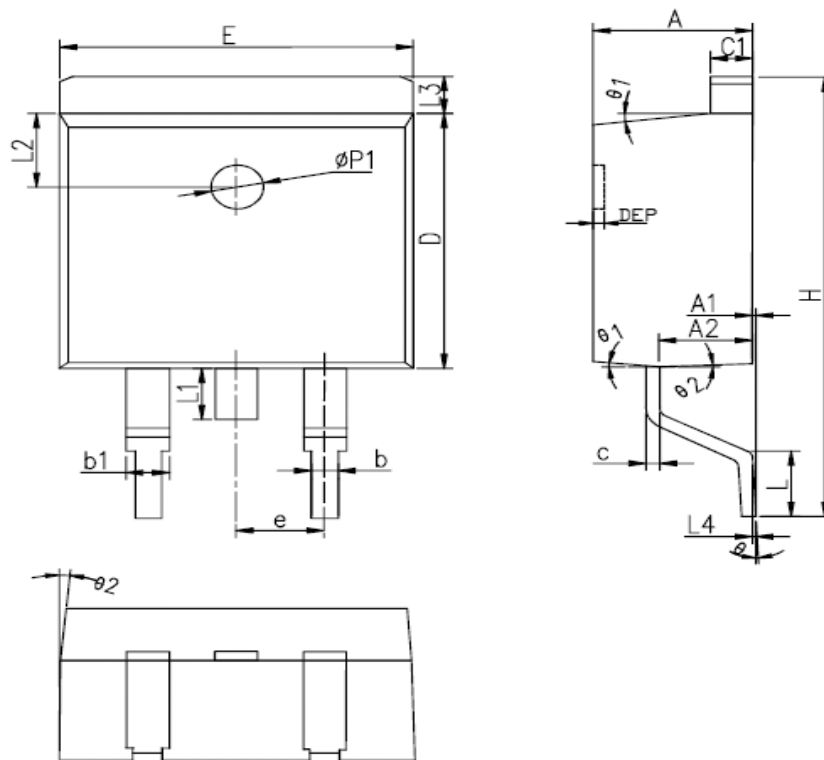
G : Green & Lead Free Device

Packaging

T : TUBE

TR : Tape & Reel

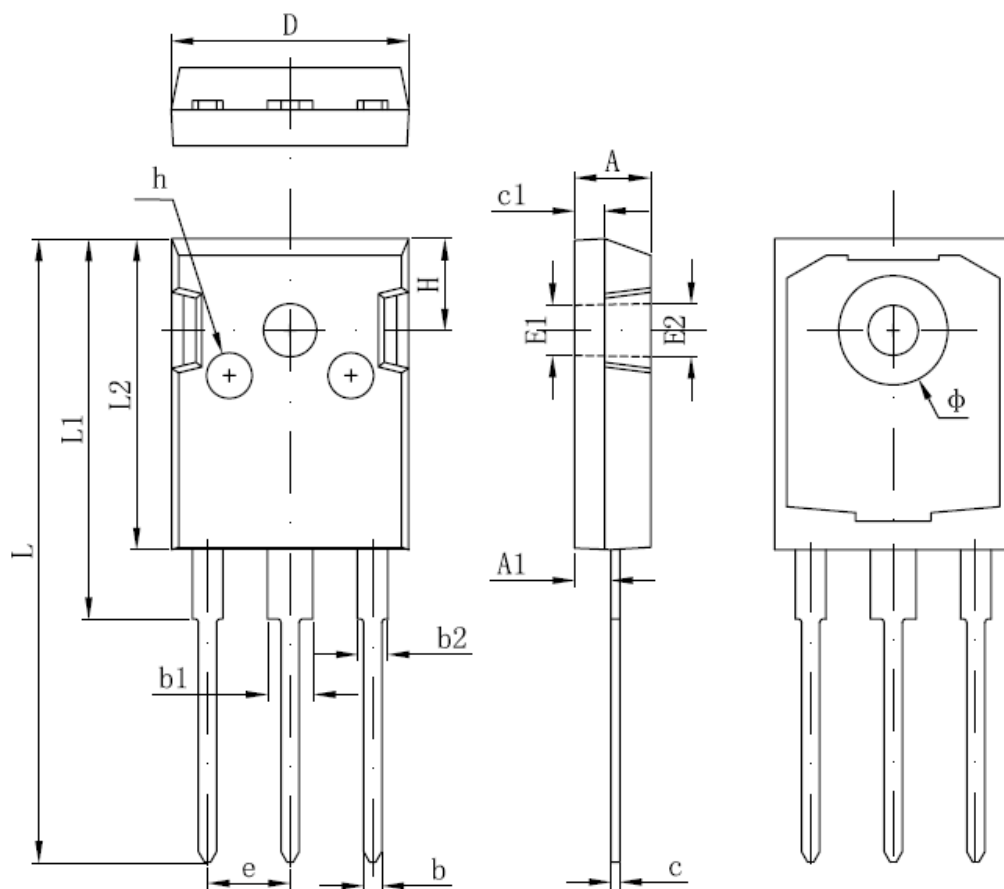
TO-263-2L



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	L	2.00	2.30	2.60	0.079	0.090	0.102
A1	0	0.10	0.25	0	0.004	0.010	L3	1.17	1.27	1.40	0.046	0.050	0.055
A2	2.59	2.69	2.79	0.102	0.106	0.110	L1	-	-	1.70	-	-	0.067
b	0.77	-	0.90	0.030	-	0.035	L4	0.25BSC			0.01BSC		
b1	1.23	-	1.36	0.048	-	0.052	L2	2.50REF.			0.098REF.		
c	0.34	-	0.47	0.013	-	0.019	θ	0°	-	8°	0°	-	8°
C1	1.22	-	1.32	0.048	-	0.052	θ 1	5°	7°	9°	5°	7°	9°
D	8.60	8.70	8.80	0.338	0.343	0.346	θ 2	1°	3°	5°	1°	3°	5°
E	10.00	10.16	10.26	0.394	0.4	0.404	DEP	0.05	0.10	0.20	0.002	0.004	0.008
e	2.54BSC			0.1BSC			Øp1	1.40	1.50	1.60	0.055	0.059	0.063
H	14.70	15.10	15.50	0.579	0.594	0.610							

**ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS**

TO-247



SYMBOL	MM		INCH		SYMBOL	MM		INCH	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	4.850	5.150	0.191	0.200	E2	3.600 REF		0.142 REF	
A1	2.200	2.600	0.087	0.102	L	40.900	41.300	1.610	1.626
B	1.000	1.400	0.039	0.055	L1	24.800	25.100	0.976	0.988
b1	2.800	3.200	0.110	0.126	L2	20.300	20.600	0.799	0.811
b2	1.800	2.200	0.071	0.087	Φ	7.100	7.300	0.280	0.287
c	0.500	0.700	0.020	0.028	e	5.450 TYP		0.215 TYP	
c1	1.900	2.100	0.075	0.083	H	5.980 REF.		0.235 REF.	
D	15.450	15.750	0.608	0.620	h	0.000	0.300	0.000	0.012
E1	3.500 REF.		0.138 REF.						

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